

#### **Features**

- Trench Power LV MOSFET Technology
- · Excellent Package for Heat Dissipation
- High Density Cell Design for Low R<sub>DS(ON)</sub>
- Moisture Sensitivity Level 1
- · Halogen Free Available Upon Request By Adding Suffix "-HF"
- · Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

## **Maximum Ratings**

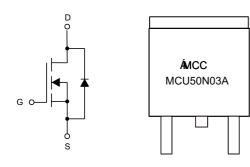
- Operating Junction Temperature Range: -55°C to +175°C
- Storage Temperature Range: -55°C to +175°C
- Thermal Resistance: 2.5°C/W Junction to Case<sup>(1)</sup>

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V <sub>DS</sub>	30	V
Gate-Source Volltage	V <sub>GS</sub>	±20	V
Continuous Drain Current	I <sub>D</sub>	50	Α
Pulsed Drain Current <sup>(2)</sup>	I <sub>DM</sub>	150	Α
Total Power Dissipation	P <sub>D</sub>	60	W
Single Pulsed Avalanche Energy	E <sub>AS</sub>	80	mJ

#### Note:

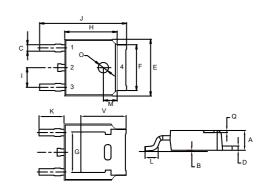
1.  $R_{\theta JA}$  is the sum of the junction-to-Case and Case-to-ambient thermal resistance, where the Case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design, while  $R_{\theta JA}$  is determined by the board design. The maximum rating presented here is based on mounting on a 1 in² pad of 2oz copper. 2. Pulse Test: Pulse Width $\leq$ 300us,Duty cycle  $\leq$ 2%.

## **Internal Structure and Marking Code**



# N-CHANNEL MOSFET

# **DPAK(TO-252)**



- Gate
- 2,4. Drain
  - 3. Source

DIMENSIONS					
DIM	INCHES		MM		NOTE
DIIVI	MIN	MAX	MIN	MAX	NOTE
Α	0.087	0.094	2.20	2.40	
В	0.000	0.005	0.00	0.13	
С	0.026	0.034	0.66	0.86	
D	0.018	0.023	0.46	0.58	
Е	0.256	0.264	6.50	6.70	
F	0.201	0.215	5.10	5.46	
G	0.190		4.83		TYP.
Н	0.236	0.244	6.00	6.20	
ı	0.086	0.094	2.18	2.39	
J	0.386	0.409	9.80	10.40	
K	0.114		2.90		TYP.
L	0.055	0.067	1.40	1.70	
М	0.063		1.60		TYP.
0	0.043	0.051	1.10	1.30	
Q	0.000	0.012	0.00	0.30	
V	0.211		5.3	35	TYP.

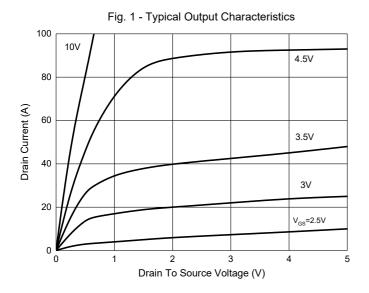


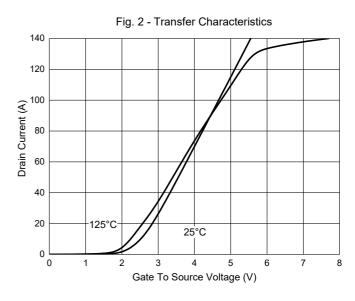
## Electrical Characteristics @ 25°C (Unless Otherwise Specified)

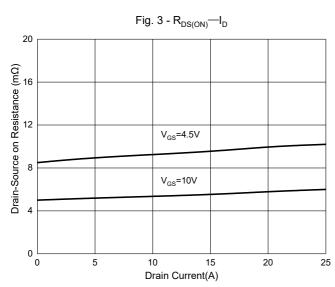
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static Characteristics						1	
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	30			V	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1	μA	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	1	1.5	2.2	V	
Dunin Course On Basistan		V <sub>GS</sub> =10V, I <sub>D</sub> =15A		5.4	7.3	mΩ	
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =15A		9.5	11.5	mΩ	
Diode Characteristics			1	1			
Continuous Body Diode Current	Is				50	Α	
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =15A			1.2	V	
Reverse Recovery Time	t <sub>rr</sub>	1 004 11/11/4004/		5		ns	
Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>S</sub> =20A, dI <sub>F</sub> /dt=100A/μs		0.2		nC	
Dynamic Characteristics						1	
Input Capacitance	C <sub>iss</sub>			1015			
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =15V,V <sub>GS</sub> =0V,f=1MHz		201		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			164		1	
Total Gate Charge	$Q_g$			23.6			
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =20V,V <sub>GS</sub> =10V,I <sub>D</sub> =20A		3.9		nC	
Gate-Drain Charge	$Q_{gd}$			7			
Turn-On Delay Time	t <sub>d(on)</sub>			7			
Turn-On Rise Time	t <sub>r</sub>	V <sub>GS</sub> =10V, V <sub>DD</sub> =20V,I <sub>D</sub> =2A		19		- ns	
Turn-Off Delay Time	t <sub>d(off)</sub>	$R_{GEN}=3\Omega$		24			
Turn-Off Fall Time	t <sub>f</sub>			24			

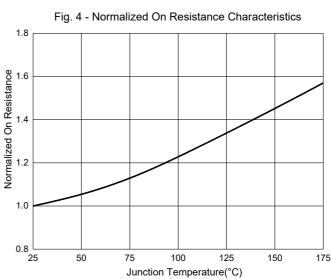


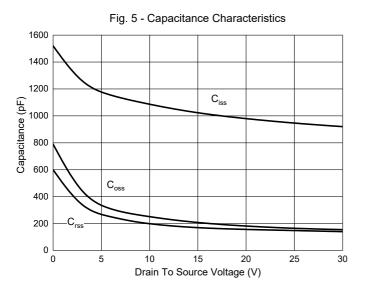
#### **Curve Characteristics**

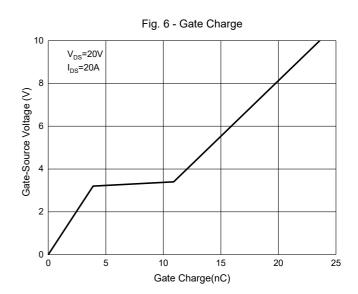








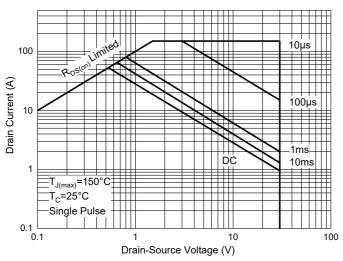






## **Curve Characteristics**







## **Ordering Information**

Device	Packing
Part Number-TP	Tape&Reel: 2.5Kpcs/Reel

Note: Adding "-HF" Suffix for Halogen Free, eg. Part Number-TP-HF

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